74AUP1G38

Low-power 2-input NAND gate (open drain)

Rev. 9 — 16 August 2022

Product data sheet

1. General description

The 74AUP1G38 is a single 2-input NAND gate with open-drain output. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times. This device ensures very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V. This device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the potentially damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- CMOS low power dissipation
- · High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8C (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- · Overvoltage tolerant inputs to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- · Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP1G38GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AUP1G38GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	<u>SOT886</u>
74AUP1G38GN	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 0.9 × 1.0 × 0.35 mm	SOT1115
74AUP1G38GS	-40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 × 1.0 × 0.35 mm	SOT1202
74AUP1G38GX	-40 °C to +125 °C	X2SON5	plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 × 0.8 × 0.32 mm	SOT1226-3

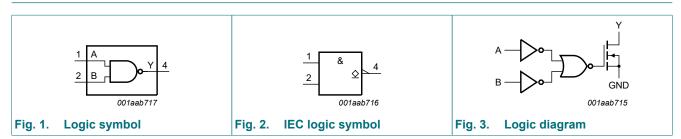
4. Marking

Table 2. Marking

Type number	Marking code[1]
74AUP1G38GW	аВ
74AUP1G38GM	аВ
74AUP1G38GN	аВ
74AUP1G38GS	аВ
74AUP1G38GX	аВ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



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6. Pinning information

6.1. Pinning





6.2. Pin description

Table 3. Pin description

Symbol	Pin	Pin			
	TSSOP5 and X2SON5	XSON6			
A	1	1	data input		
В	2	2	data input		
GND	3	3	ground (0 V)		
Υ	4	4	data output		
n.c.	-	5	not connected		
V _{CC}	5	6	supply voltage		

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7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state.

Input	Output	
A	В	Υ
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[1]	-0.5	+4.6	V
I _O	output current	V _O = 0 V to V _{CC}		-	+20	mA
I _{CC}	supply current			-	+50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	[2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

^[2] For SOT353-1 (TSSOP5) package: P_{tot} derates linearly with 3.3 mW/K above 74 °C.

For SOT886 (XSON6) package: P_{tot} derates linearly with 3.3 mW/K above 74 °C.

For SOT1115 (XSON6) package: Ptot derates linearly with 3.2 mW/K above 71 °C.

For SOT1202 (XSON6) package: P_{tot} derates linearly with 3.3 mW/K above 74 °C.

For SOT1226-3 (X2SON5) package: Ptot derates linearly with 3.0 mW/K above 67 °C.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	8.0	-	pF
Co	output capacitance	output enabled; V _O = GND; V _{CC} = 0 V	-	1.7	-	pF
		output disabled; V _O = GND; V _{CC} = 0 V	-	1.1	-	pF

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C				1	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$		-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
l _l	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V to } 3.6 \text{ V; } V_{CC} = 0 \text{ V}$	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C				1	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH}$ or V_{IL}				
		I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.36	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.50	V
l _l	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 0 \text{ V to } 3.6 \text{ V; } V_{CC} = 0 \text{ V}$	-	-	±0.75	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Fig. 9.

Symbol	Parameter	Conditions		25 °C		-40 °C to	o +85 °C	-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
C _L = 5 p	F									
t _{pd}		A or B to Y; see Fig. 8 [2]								
	delay	V _{CC} = 0.8 V	-	13.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.9	4.6	10.4	1.8	11.4	1.8	12.6	ns
		V _{CC} = 1.4 V to 1.6 V	1.5	3.3	6.5	1.4	7.4	1.4	8.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.2	2.9	5.1	1.1	5.9	1.1	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.2	3.8	0.9	4.5	0.9	4.9	ns
		V _{CC} = 3.0 V to 3.6 V	0.9	2.3	4.0	0.8	4.5	0.8	4.9	ns
C _L = 10	pF									
t _{pd}	propagation	A or B to Y; see Fig. 8 [2]								
	delay	V _{CC} = 0.8 V	-	16.3	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.3	5.6	12.3	2.1	13.7	2.1	15.1	ns
		V _{CC} = 1.4 V to 1.6 V	1.8	4.1	7.6	1.7	8.8	1.7	9.7	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.8	6.1	1.4	7.1	1.4	7.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.9	4.6	1.2	5.4	1.2	5.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	3.2	5.7	1.1	6.4	1.1	7.0	ns
C _L = 15	pF					'				
t _{pd}	propagation	A or B to Y; see Fig. 8 [2]								
	delay	V _{CC} = 0.8 V	-	19.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	6.6	14.2	2.4	15.8	2.4	17.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.8	8.7	1.9	10.1	1.9	11.1	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	4.6	7.6	1.7	8.5	1.7	9.3	ns
		V _{CC} = 2.3 V to 2.7 V	1.6	3.6	5.6	1.5	6.3	1.5	6.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	4.1	7.5	1.4	8.3	1.4	9.1	ns
C _L = 30	pF									
t _{pd}		A or B to Y; see Fig. 8 [2]								
	delay	V _{CC} = 0.8 V	-	27.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	9.5	19.5	3.2	21.8	3.2	24.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	7.0	11.5	2.6	13.6	2.6	15.0	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	7.0	12.1	2.3	13.3	2.3	14.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	5.4	8.9	2.1	9.9	2.1	10.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	6.5	12.7	2.1	13.9	2.1	15.3	ns

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Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		C -40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	
C _L = 5 p	F, 10 pF, 15 p	F and 30 pF								
C _{PD}	power dissipation	f_i = 1 MHz; [3] V_I = GND to V_{CC}								
	capacitance	V _{CC} = 0.8 V	-	0.6	-	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	0.7	-	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	0.8	-	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	0.9	-	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	1.1	-	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	1.4	-	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PZL} and t_{PLZ} .
- [3] \dot{C}_{PD} is used to determine the dynamic power dissipation (\dot{P}_{D} in μW).

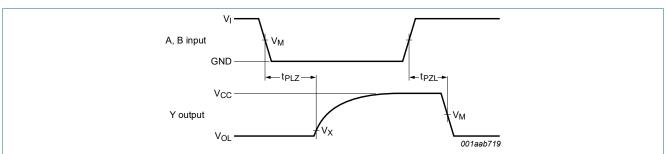
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

11.1. Waveforms and test circuit



Measurement points are given in Table 9.

Logic levels: V_{OL} is a typical output voltage drop that occur with the output load.

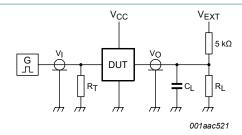
Fig. 8. The data input (A or B) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Input			Output		
V _{CC}	V _M	V _I	$t_r = t_f$	V _M	V _X	
0.8 V to 1.6 V	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns	0.5 × V _{CC}	V _{OL} + 0.1 V	
1.65 V to 2.7 V	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns	0.5 × V _{CC}	V _{OL} + 0.15 V	
3.0 V to 3.6 V	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns	0.5 × V _{CC}	V _{OL} + 0.3 V	

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Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance;

C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator;

 V_{EXT} = External voltage for measuring switching times.

Fig. 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}

[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

Low-power 2-input NAND gate (open drain)

12. Package outline

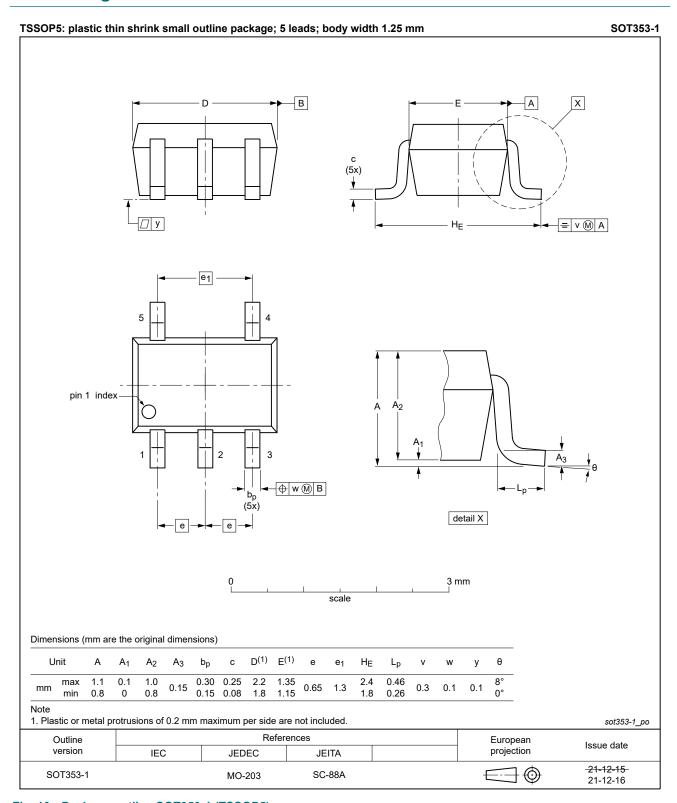


Fig. 10. Package outline SOT353-1 (TSSOP5)

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Low-power 2-input NAND gate (open drain)

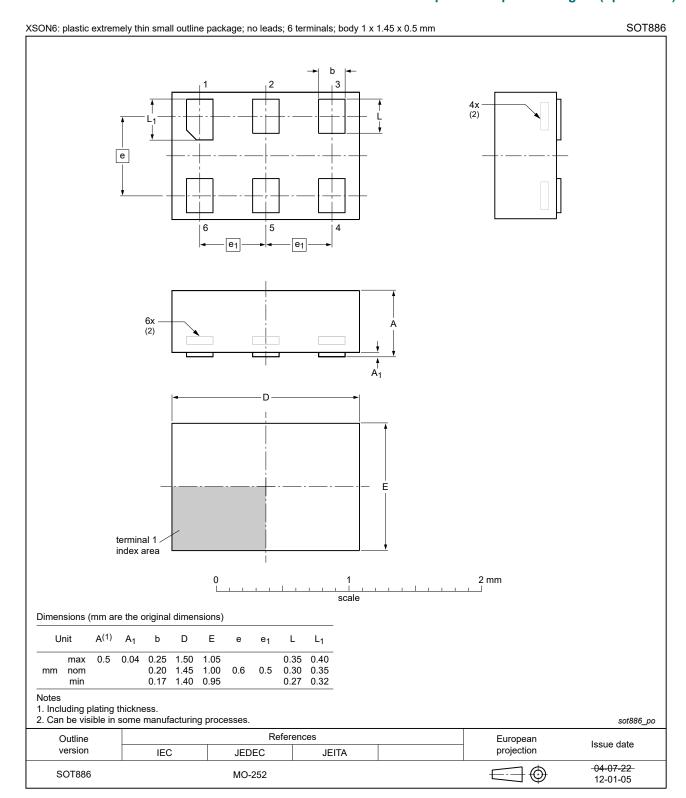


Fig. 11. Package outline SOT886 (XSON6)

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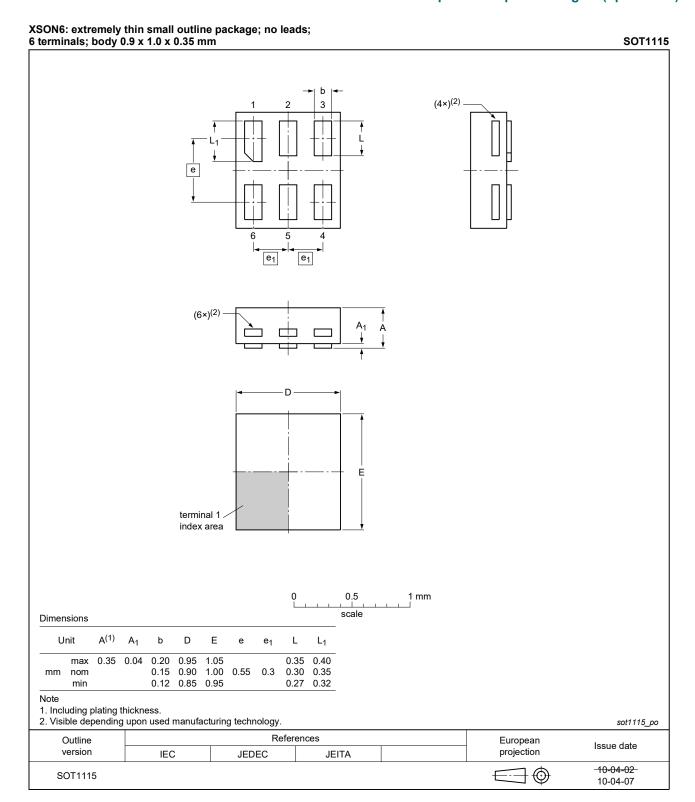


Fig. 12. Package outline SOT1115 (XSON6)

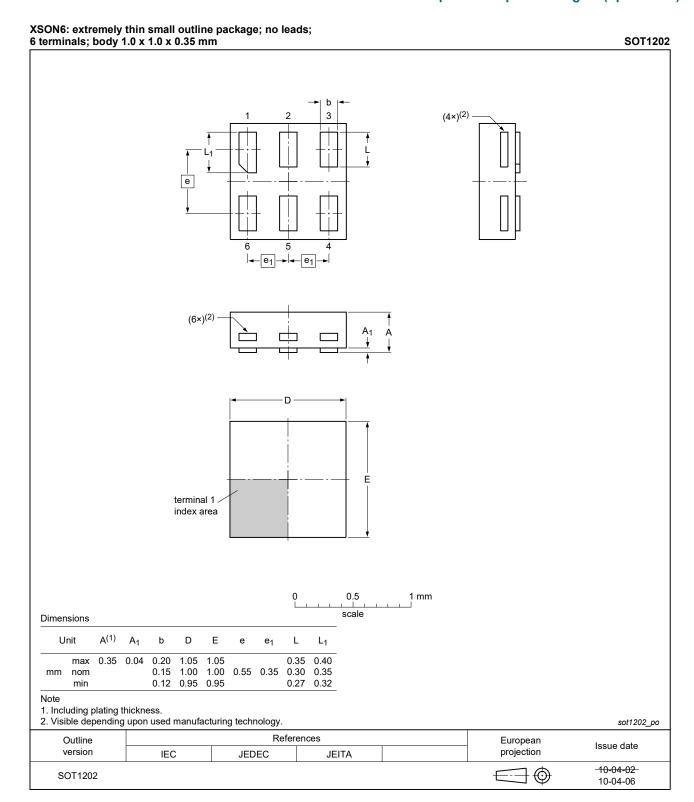


Fig. 13. Package outline SOT1202 (XSON6)

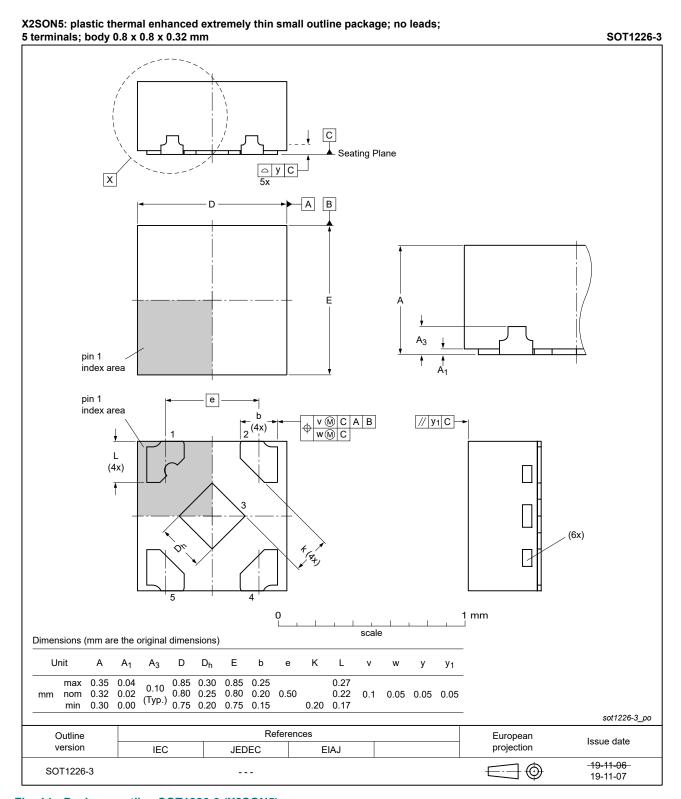


Fig. 14. Package outline SOT1226-3 (X2SON5)

Low-power 2-input NAND gate (open drain)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AUP1G38 v.9	20220816	Product data sheet	-	74AUP1G38 v.8	
Modifications:	 Package SOT 	Package SOT1226 (X2SON5) changed to SOT1226-3 (X2SON5).			
74AUP1G38 v.8	20220207	Product data sheet	-	74AUP1G38 v.7	
Modifications:	Nexperia. Legal texts ha Fig. 10: Packa Type number Section 1 and	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Fig. 10: Package outline drawing for SOT353-1 (TSSOP5) has changed. Type number 74AUP1G38GF (SOT891/ XSON6) removed. Section 1 and Section 2 updated. Table 5: Derating values for Ptot total power dissipation updated. 			
74AUP1G38 v.7	20160404	Product data sheet	-	74AUP1G38 v.6	
Modifications:	• <u>Fig. 7</u> : Typo co	Fig. 7: Typo corrected in pin naming (pins A and B swapped)			
74AUP1G38 v.6	20120628	Product data sheet	-	74AUP1G38 v.5	
Modifications:	 Added type number 74AUP1G38GX (SOT1226) Package outline drawing of SOT886 (Fig. 11) modified. 				
74AUP1G38 v.5	20111129	Product data sheet	-	74AUP1G38 v.4	
Modifications:	 Legal pages u 	Legal pages updated.			
74AUP1G38 v.4	20101007	Product data sheet	-	74AUP1G38 v.3	
74AUP1G38 v.3	20090622	Product data sheet	-	74AUP1G38 v.2	
74AUP1G38 v.2	20070614	Product data sheet	-	74AUP1G38 v.1	
74AUP1G38 v.1	20061020	Product data sheet	-	-	

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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